

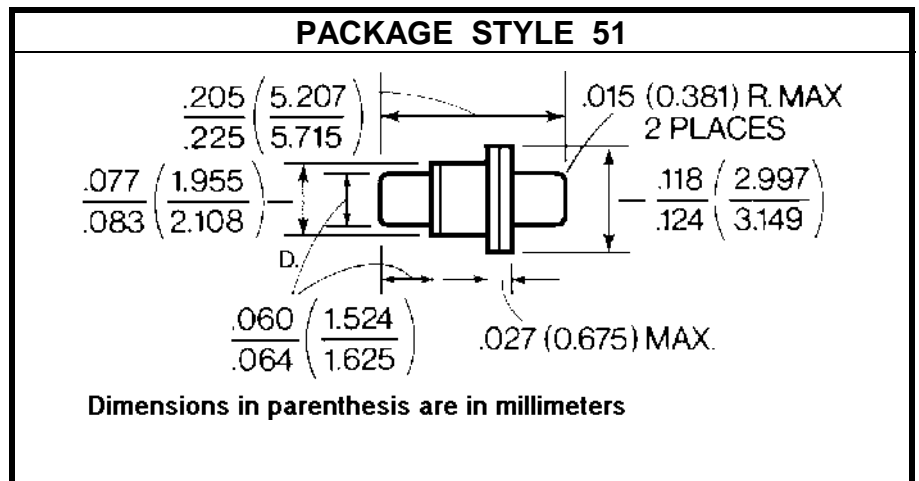
SILICON MULTIPLIER DIODE

DESCRIPTION:

The **ASI BXY56** is a Varactor Diode Designed for Operation in Low and High Order Multiplier Circuits.

MAXIMUM RATINGS

I_C	100 mA
V_{CE}	60 V
P_{DISS}	5.2 W @ T _C = 50 °C
T_J	-55 °C to +175 °C
T_{STG}	-55 °C to +175 °C
θ_{JC}	24 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
V_B	I _R = 10 μA	60			V
C_j	V _R = -6.0 V f = 1.0 MHz	1.5		2.5	pF
f_{c-6}	V _R = 6.0 V f = 10 GHz	160			GHz
T_i	6.0 mA / 10 mA		60		μS
T_t	10 V / 10 mA			350	pS
MARKING	INK DOT INDICATES CATHODE END				